## Dielectric and magnetic birefringence in Zn<sub>1-x</sub>Mn<sub>x</sub>Se

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Results

x = 0.14

Litvino

x = 0.00

Formation of wurtzite planes normal

dielectric birefringence in dependance

the Mn concentration x. At x = 0.3 a

sphalerite to the wurtzite structure

to the [111] direction causes

phase transformation from the

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Interaction between long wavelength electromagnetic radiation and bound and unbound electrical charge carriers subjected to an external magnetic field causes optical birefringence precisely measurable using generalized ellipsometry. ZnSe is an important II-VI semiconductor with a variety of applications in optoelectronic devices.



Zn, Mn 💿 🔹 Se

possesses a temperature dependent magnetic moment as well as remarkable magnetooptic (MO) properties, which in conjunction with the electronic properties suggest future applications for MO and spintronic devices.









Landau shift.		
X <sub>Mn</sub>	$\frac{ E_c(\pm 3/2) - E_v(\pm 1/2) }{1 \times 10^{-4} \text{ eV}}$	$E_L$ 1×10 <sup>-4</sup> eV
0.02	2 (1)	1.1 (3)
0.13	8 (3)	1.2 (5)
0.28	12 (3)	1.0 (4)

Loop measurements in dependance of the magnetic field can also be modeled.



Experiment

## Mueller matrix

Generalized Ellipsometry measures the general optical polarization response of samples in terms of Mueller matrix elements, and allows for reconstruction of the permittivity, permeability, and magnetoelectric response tensors.



Our message

We studied the dielectric and magnetic-field induced anisotropic optical properties of  $Zn_{+x}Mn_x$ Se thin films with generalized spectroscopic ellipsometry in the VIS-UV spectral range for Mn concentrations of x = 0.00, 0.02, 0.13and 0.28. The dielectric and the magnetic field induced anisotropies in  $Zn_{+x}Mn_x$ Se were treated separately into the diagonal and off-diagonal components of the dielectric tensor.

We are able to quantify the shift of the band gap energy between the DF parallel and perpendicular to the optical axis caused by the formation of wurtzite domains with increasing x.

The optical anisotropy occurs in the direction [111], which is in good concordance with previous TEM investigations. The dielectric anisotropy results in a red shift of the energy band gap parallel to the optical axis with a maximum for x = 0.13.

Measurements of the sp-d exchange energy at room temperature are presented and found a maximum value for the sample with maximum Mn concentration x = 0.28.

MRSEC Q-SPINS Meeting, Lincoln, NE, October 5, 2007 54<sup>th</sup> Midwest Semiconductor Conference, Lincoln, NE, October 6-7, 2007